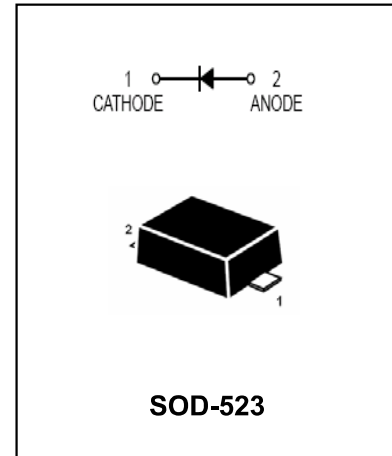


Features

- Low forward voltage drop.
- Guard ring construction for transient protection.
- Low reverse recovery time.
- Low reverse capacitance.
- Compliant to Halogen-free.
- Suffix "-Q1" for AEC-Q101



Applications

- Schottky barrier application.

Ordering Information

- Marking:S4

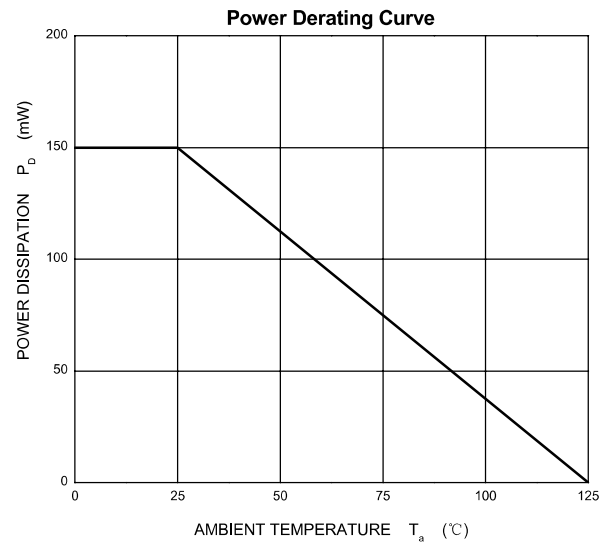
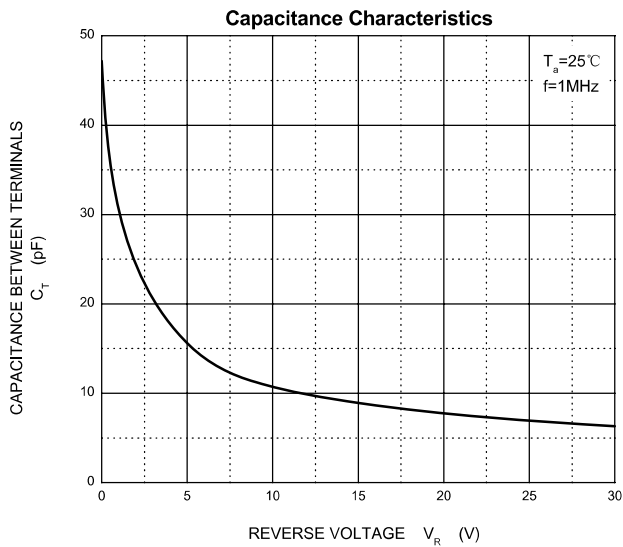
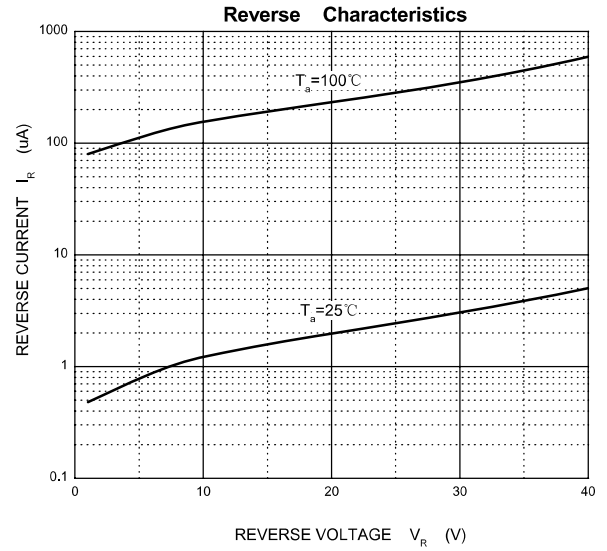
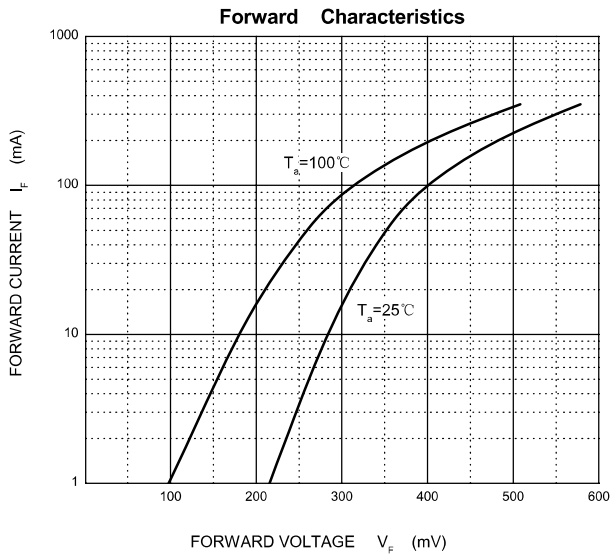
Maximum Rating @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
DC Reverse voltage	V_R	40	V
Continuous forward current	I_F	350	mA
Repetitive peak forward current @t≤1.0s	I_{FRM}	1	A
Total power dissipation	P_{tot}	400	mW
Total resistance junction to ambient	$R_{\theta JA}$	300	°C/W
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-65-125	°C

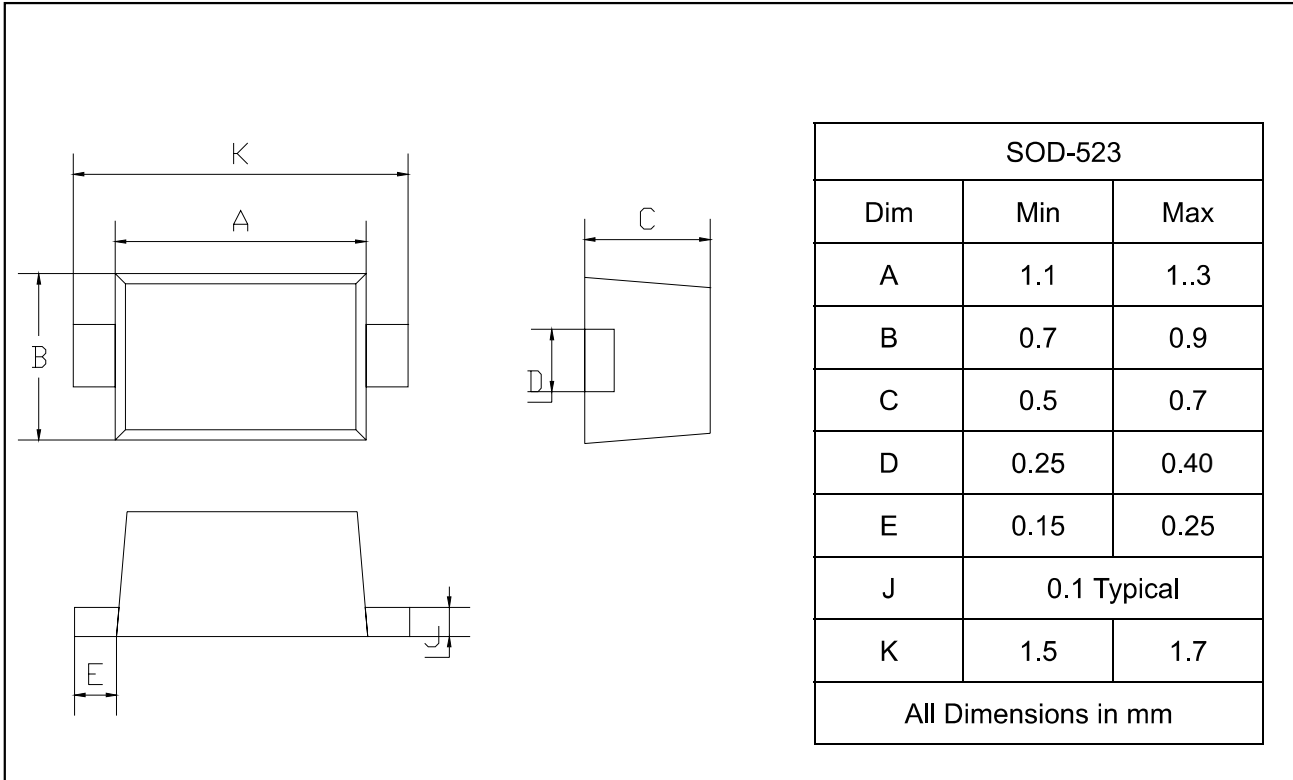
Electrical Characteristics @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)R}$	40			V	$I_R=100\mu A$
Forward voltage	V_F			0.37 0.60	V	$I_F=20mA$ $I_F=200mA$
Reverse current	I_R			5.0	μA	$V_R=30V$
Diode capacitance	C_d		50		pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}		10		ns	$I_F=I_R=50mA, R_L=100\Omega$

Typical Characteristics



Package Outline



Soldering Footprint

